

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1220	(438/592).CCLS.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/20 09:19
S2	349	S1 and (MOSFET)	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 14:12
S3	353	S1 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/19 10:33
S6	327	(438/294).CCLS.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/16 14:58
S7	103	S6 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 15:26
S9	714	(438/296).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/16 15:26
S10	171	S9 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 16:04
S11	1453	(438/424).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/16 16:04
S12	225	S11 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 16:39
S13	222	S12 and (trench near\$5 isolat\$5)	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 16:40
S14	1128	(438/197).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/16 16:39
S15	434	S14 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 16:39

S16	343	S15 and (trench near\$5 isolat\$5)	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/16 16:40
S17	0	("2004/0126948").URPN.	USPAT	OR	ON	2005/05/16 17:08
S18	0	("2004/0126948").URPN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 17:08
S19	0	("2004/0126948").URPN.	USPAT	OR	ON	2005/05/17 11:58
S25	1	("6689664").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/17 13:11
S26	177	(438/218).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/17 13:22
S27	80849	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 13:22
S28	1230	S27 and (recess groove trench opening) same gate same (W tungsten refractory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 13:25
S29	1113	S28 and ("257"/\$.ccls. or "438"/\$.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 13:26
S30	1	S28 and (barrier refractory) same oxid\$5 same prevent\$3 same (extigate extend\$5 near5 trench near5 isolat\$3 near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 13:29
S31	1	S27 and (barrier refractory) same oxid\$5 same prevent\$3 same (extigate extend\$5 near5 trench near5 isolat\$3 near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 13:30
S32	477	S27 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:12

S33	77	S28 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:05
S34	13	S29 and (extigate extend\$5 near5 trench near5 isolat\$4 near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:11
S35	11	S29 and (extend\$5 near5 trench near5 isolat\$4 near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:11
S36	76	S29 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:14
S37	993	S29 and oxid\$5 near7 (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:15
S38	3	S37 and extigate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:15
S39	404	S29 and (barrier refractory) same oxid\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:16
S40	382	S39 and oxid\$5 near7 (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 14:17
S41	244	S39 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:27
S42	1	("4685196").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/17 15:53

S43	3180	S27 and (prevent\$3 inhibit\$3) same (short\$3 near3 (electrical circuit) resist\$5 near3 (increas\$3 ris\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:57
S44	50	S43 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 16:06
S45	3010	S43 and (gate semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 16:07
S46	2	S43 and extigate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 16:07
S47	76	(438/219).CCLS.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/18 10:35
S48	314	(438/221).CCLS.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/18 10:36
S49	74	S48 and MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 10:47
S50	135	(438/223).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/18 14:12
S51	227	(438/230).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/18 14:12
S52	80849	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:35
S53	4	S52 and EXTIGATE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:35

S54	42	S52 and (EXTIGATE extend\$5 near5 trench near5 isolat\$3 near5 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:37
S55	1	("20040075138").PN.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/19 10:03
S56	1	("6838326").PN.	US-PGPUB; USPAT; USOCR; JPO	OR	OFF	2005/05/19 10:32
S57	1185	(438/303).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/19 10:32
S58	473	S57 and MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 10:33
S59	483	S57 and (MOSFET or "metal oxide semiconductor field effect transistor")	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2005/05/19 13:42
S60	510	(438/299).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/19 13:42
S61	507	(438/299).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/19 13:42
S62	186	S60 and MOSFET	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/19 15:44
S63	907	(438/275).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/19 15:44
S64	251	S63 and MOSFET	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 10:24
S65	1058	(438/287).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/20 10:25

S66	253	S65 and MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:25
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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	61528	mosfet metal adj oxide near5 field adj effect	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 10:53
L3	3738	2 and (trench opening groove recess hole) near5 fill\$3 near5 (isolat\$3 dielectric insulating oxide dioxide nitride sin sio2 "sio?sub.2" n>"sub.4")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:00
L4	859	3 and (oxide dioxide sio2 "sio?sub.2" ) same (sidewall wall) near7 (polysilicon silicon) same gate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:21
L5	799	4 and (trench opening groove recess hole) same gate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:01
L6	8	5 and (prevent\$3 eliminat\$3 inhibit\$3) near7 oxid\$5 near5 (metal barrier) same (w tungsten)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:04
L7	8	6 and (prevent\$3 eliminat\$3 inhibit\$3) near7 oxid\$5 near5 (metal barrier)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:04
L8	8776	("257"/\$.ccls. "438"/\$.ccls. "427"/\$.ccls.) and (sti trench near3 isolat\$4) same gate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:17
L9	3136	8 and (sti trench near3 isolat\$4) near7 (etch\$3 recess\$3 remov\$3)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:19
L10	615	9 and fill\$3 near5 (sti isolat\$4) near7 (etch\$3 recess\$3 remov\$3)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:20
L11	115	10 and (oxide dioxide sio2 "sio?sub.2" ) same (sidewall wall) near7 (polysilicon silicon) same gate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/05/23 11:21
L12	100	11 not (@rlad>"20031215" @ad>"20031215")	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/05/23 11:22